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--12. The production method according to Claim 10, wherein the removal of the peripheral portion of the thin film is attained by removing a region of 1-5 mm from the peripheral end of the base wafer.--

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--13. The production method according to Claim 11, wherein the removal of the peripheral portion of the thin film is attained by removing at least the SOI layer for a region of 1-5 mm from the peripheral end of the base wafer.--

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--14. The production method according to Claim 10, wherein the removal of the peripheral portion of the thin film is attained by etching the wafer with masking at least portions of the top surface other than the peripheral portion to be removed.--

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--15. The production method according to Claim 12, wherein the removal of the peripheral portion of the thin film is attained by etching the wafer with masking at least portions of the top surface other than the peripheral portion to be removed.--

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--16. The production method according to Claim 13, wherein the removal of the peripheral portion of the thin film is attained by etching the wafer with masking at least portions of the top surface other than the peripheral portion to be removed.--

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--17. The production method according Claim 10, wherein the removal of the peripheral portion of the thin film is attained by holding together a plurality of wafers stacked so that at least the peripheral portions to be removed should be exposed, and etching them.--

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--18. The production method according Claim 12, wherein the removal of the peripheral portion of the thin film is attained by holding together a plurality of wafers stacked so that at least the peripheral portions to be removed should be exposed, and etching them.--

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--19. The production method according Claim 13, wherein the removal of the peripheral portion of the thin film is attained by holding together a plurality of wafers stacked so that at least the peripheral portions to be removed should be exposed, and etching them.--

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--20. The production method according to Claim 10, wherein the removal of the peripheral portion of the thin film is attained by polishing only the peripheral portion.--